

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT  
APPLICATIONREQUEST FOR FILING APPLICATION  
Under Rule 53(a), (b) & (f)  
(N Filing Fee or Oath/Declaration)  
(Do NOT use for Provisional or PCT Applications)  
Use for Design or Utility Applications

00909

**RULE 53(f) NO DECLARATION**Hon. Commissioner of Patents  
Washington, DC 20231

Atty. Dkt.

P 2800192

M#

EL00028CDC

Client Ref

Date:

April 17, 2001

Sir:

1. This is a Request for filing a new Patent Application(☐ Design ☒ Utility) entitled:

2. (Complete) Title:

FABRICATING PROCESS OF A SEMICONDUCTOR DEVICE INCLUDING A CVD  
PROCESS OF A METAL FILMwithout a filing fee or Oath/Declaration but for which is enclosed the following:3. ☒ Abstract 1 page(s).4. 24 Pages of Specification (only spec. and claims);5. ☐ Specification in non-English language6. 14 Numbered claim(s); and7. ☒ Drawings: 13 sheet(s) ☐ 1 set informal;8. ☒ formal of size: ☒ A4 ☐ 11"9. **DOMESTIC/INTERNATIONAL** priority is claimed under 35 USC 119(e)/120/365(c) based on the following provisional, nonprovisional and/or PCT international application(s):

| Application No. | Filing Date | Application No. | Filing Date |
|-----------------|-------------|-----------------|-------------|
| (1)             |             | (2)             |             |
| (3)             |             | (4)             |             |
| (5)             |             | (6)             |             |

10. **FOREIGN** priority is claimed under 35 USC 119(a)-(d)/365(b) based on filing in

JAPAN

| Application No. | Filing Date    | Application No.   | Filing Date |
|-----------------|----------------|---|-------------|
| (1) 2000-115187 | April 17, 2000 | (2)   |             |
| (3)             |                | (4)   |             |
| (5)             |                | <input type="checkbox"/> See 3 <sup>rd</sup> page for additional priorities |             |

11. 1 (No.) Certified copy (copies): ☒ attached; ☐ previously filed (date) \_\_\_\_\_  
in U.S. Application No. \_\_\_\_\_ / filed on \_\_\_\_\_12. ☐ This is a reissue of Patent No. \_\_\_\_\_13. ☐ See top first page re prior Provisional, National, International application(s) (X box only if info is there and do not complete item 14 or 15.)

14. This application claims benefit of the following prior US application(s), the contents of which are incorporated into this application by this reference:

|         |   |       |  |
|---------|---|-------|--|
| No.     | / | filed |  |
| No.     | / | filed |  |
| No.     | / | filed |  |
| No. PCT | / | filed |  |

Designated the U.S. and that International Application ☐ was ☐ was not published under PCT Article 21(2) in English15. ☐ See the attached Preliminary Amendment, which amends the specification to claim benefit of the above listed US applications16. Extension to date: ☐ concurrently filed ☐ not needed ☐ previously filed17. ☐ Small Entity Status is claimed (**pre-filing confirmation required**)17(a) ☐ Attached: (No.) Small Entity Statement(s). (Since 9/8/00 Small Entity Statement not essential to make claim)17(b) ☐ See **NONPUBLICATION REQUEST** under Rule 213(a) attached (Pat-258)

18. ☐ Assignee (optional): \_\_\_\_\_

19. ☐ Attached:

20. This application is made by the following named inventor(s) (Double check instructions for accuracy.):  
(Listing of inventor(s) not a requirement, but list if known)

|                    |  |                       |                        |
|--------------------|--|-----------------------|------------------------|
| (1) Inventor       | Tomohisa   |                       | HOSINO                 |
|                    | First  | Middle Initial        | Family Name            |
| Residence          | Nirasaki-shi, Yamanashi  | JAPAN                 | JAPAN                  |
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| (include Zip Code) |  |                       |                        |

|                    |  |                       |                        |
|--------------------|--|-----------------------|------------------------|
| (2) Inventor       | Vincent  |                       | VEZIN                  |
|                    | First  | Middle Initial        | Family Name            |
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|                    |  |                       |                        |
|--------------------|--|-----------------------|------------------------|
| (3) Inventor       | Gishi  |                       | CHUNG                  |
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| (include Zip Code) |  |                       |                        |

|                    |       |                       |                        |
|--------------------|-------|-----------------------|------------------------|
| (4) Inventor       |       |                       |                        |
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| Residence          |       |                       |                        |
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| Mailing Address    |       |                       |                        |
| (include Zip Code) |       |                       |                        |

|                    |       |                       |                        |
|--------------------|-------|-----------------------|------------------------|
| (5) Inventor       |       |                       |                        |
|                    | First | Middle Initial        | Family Name            |
| Residence          |       |                       |                        |
|                    | City  | State/Foreign Country | Country of Citizenship |
| Mailing Address    |       |                       |                        |
| (include Zip Code) |       |                       |                        |

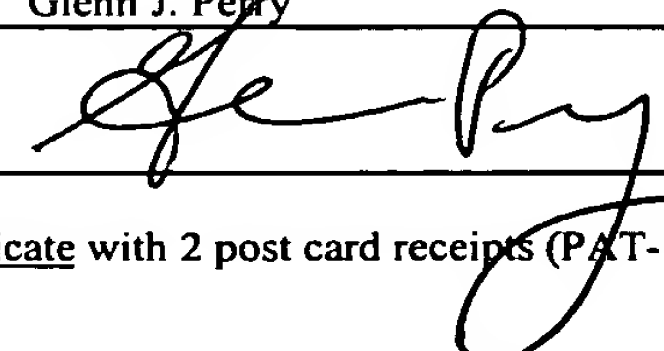
21. NOTE: FOR ADDITIONAL INVENTORS, "X" ☐ and list additional inventors on attached sheet (incorporated by reference)

Pillsbury Winthrop LLP  
Intellectual Property Group



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By: Atty: Glenn J. Perry Reg. No. 28458

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Atty/Sec: gjp/mjb

NOTE: File in duplicate with 2 post card receipts (PAT-103) & attachments

# APPLICATION UNDER UNITED STATES PATENT LAWS

Atty. Dkt. No. PW 280192  
(M#)

Invention: FABRICATING PROCESS OF A SEMICONDUCTOR DEVICE INCLUDING A CVD  
PROCESS OF A METAL FILM

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This is a:

- ☐ Provisional Application
- ☒ Regular Utility Application
- ☐ Continuing Application
  - ☐ The contents of the parent are incorporated by reference
- ☐ PCT National Phase Application
- ☐ Design Application
- ☐ Reissue Application
- ☐ Plant Application
- ☐ Substitute Specification
  - Sub. Spec Filed \_\_\_\_\_
  - in App. No. \_\_\_\_\_ / \_\_\_\_\_
- ☐ Marked up Specification re
  - Sub. Spec. filed \_\_\_\_\_
  - In App. No \_\_\_\_\_ / \_\_\_\_\_

## SPECIFICATION